MJ21193 - PNP MJ21194 - NPN

Silicon Power Transistors

The MJ21193 (PNP) and MJ21194 (NPN) utilize Perforated Emitter technology and are specifically designed for high power audio output, disk head positioners and linear applications.

Features

- Total Harmonic Distortion Characterized
- High DC Current Gain
- Excellent Gain Linearity
- High SOA
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	250	Vdc
Collector-Base Voltage	V _{CBO}	400	Vdc
Emitter-Base Voltage	V _{EBO}	5	Vdc
Collector-Emitter Voltage - 1.5 V	V _{CEX}	400	Vdc
Collector Current – Continuous	Ι _C	16	Adc
Collector Current – Peak (Note 1)	I _{CM}	30	Adc
Base Current – Continuous	Ι _Β	5	Adc
Total Power Dissipation @ T _C = 25°C Derate Above 25°C	PD	250 1.43	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	– 65 to +200	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. Pulse Test: Pulse Width = 5 μ s, Duty Cycle \leq 10%. (continued)

THERMAL CHARACTERISTICS

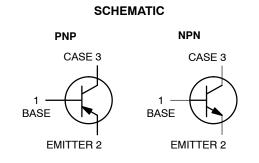
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.7	°C/W

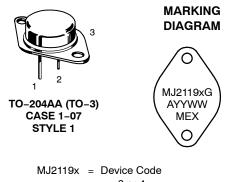


ON Semiconductor®

http://onsemi.com

16 AMP COMPLEMENTARY SILICON POWER TRANSISTORS 250 VOLTS, 250 WATTS





		201100 0000
		x = 3 or 4
G	=	Pb-Free Package
A	=	Assembly Location
YY	=	Year
WW	=	Work Week
MEX	=	Country of Origin

ORDERING INFORMATION

Device	Package	Shipping [†]
MJ21193G	TO-3 (Pb-Free)	100 Units / Tray
MJ21194G	TO-3 (Pb-Free)	100 Units / Tray

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

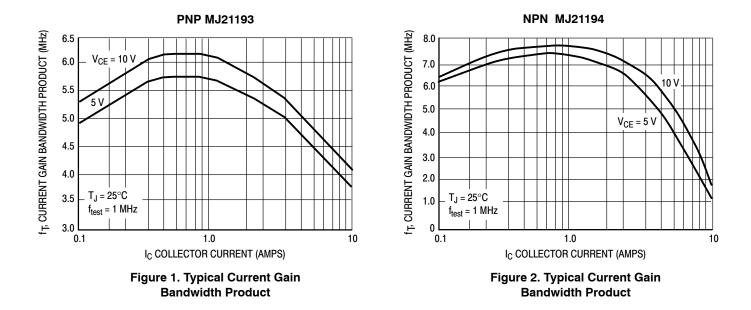
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MJ21193 - PNP MJ21194 - NPN

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	L		1		
Collector–Emitter Sustaining Voltage $(I_C = 100 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	250	-	-	Vdc
Collector Cutoff Current ($V_{CE} = 200 \text{ Vdc}, I_B = 0$)	I _{CEO}	-	-	100	μAdc
Emitter Cutoff Current ($V_{CE} = 5 \text{ Vdc}, I_C = 0$)	I _{EBO}	-	-	100	μAdc
Collector Cutoff Current (V _{CE} = 250 Vdc, V _{BE(off)} = 1.5 Vdc)	I _{CEX}	-		100	μAdc
SECOND BREAKDOWN	L.				
Second Breakdown Collector Current with Base Forward Biased ($V_{CE} = 50$ Vdc, t = 1 s (non-repetitive) ($V_{CE} = 80$ Vdc, t = 1 s (non-repetitive)	I _{S/b}	5 2.5			Adc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 8 \text{ Adc}, V_{CE} = 5 \text{ Vdc}$) ($I_C = 16 \text{ Adc}, I_B = 5 \text{ Adc}$)	h _{FE}	25 8		75	
Base-Emitter On Voltage (I _C = 8 Adc, V _{CE} = 5 Vdc)	V _{BE(on)}	-	-	2.2	Vdc
Collector–Emitter Saturation Voltage ($I_C = 8 \text{ Adc}, I_B = 0.8 \text{ Adc}$) ($I_C = 16 \text{ Adc}, I_B = 3.2 \text{ Adc}$)	V _{CE(sat)}			1.4 4	Vdc
DYNAMIC CHARACTERISTICS					
Total Harmonic Distortion at the Output V _{RMS} = 28.3 V, f = 1 kHz, P _{LOAD} = 100 W _{RMS} h _{FE} unmatched	T _{HD}		0.8		%
(Matched pair $h_{FE} = 50 @ 5 A/5 V$) h_{FE} matched		_	0.08	_	
Current Gain Bandwidth Product $(I_C = 1 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f_{test} = 1 \text{ MHz})$	f _T	4	-	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz)	C _{ob}	-	-	500	pF

NOTE: Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2%



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TYPICAL CHARACTERISTICS

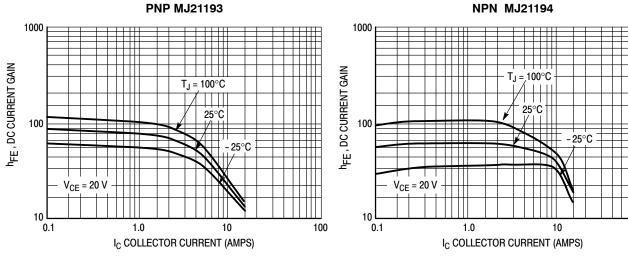
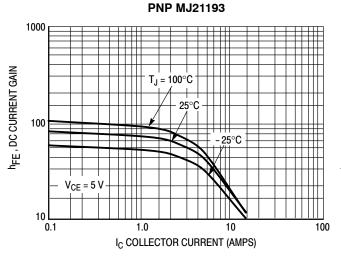


Figure 3. DC Current Gain, V_{CE} = 20 V



100





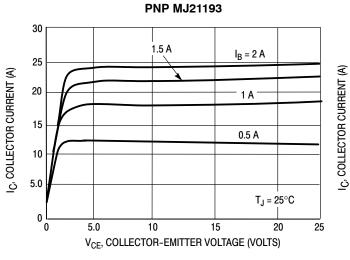
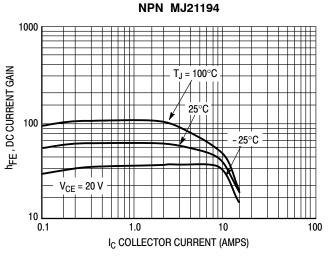
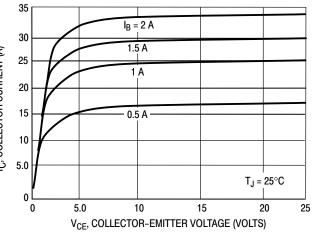


Figure 7. Typical Output Characteristics



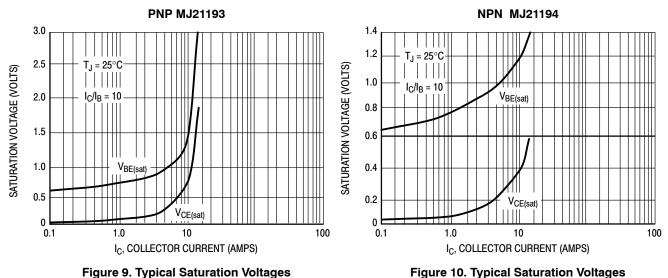








TYPICAL CHARACTERISTICS





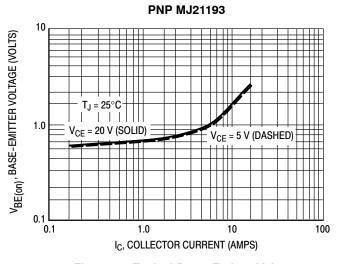


Figure 11. Typical Base-Emitter Voltage

NPN MJ21194

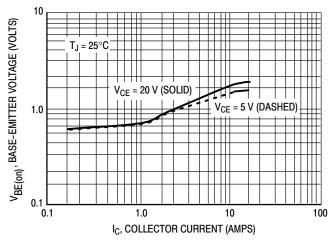


Figure 12. Typical Base-Emitter Voltage

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 13 is based on $T_{J(pk)} = 200^{\circ}C$; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

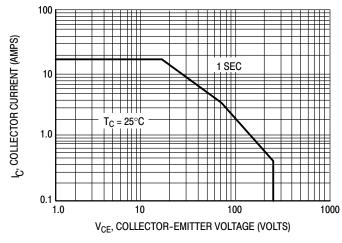


Figure 13. Active Region Safe Operating Area

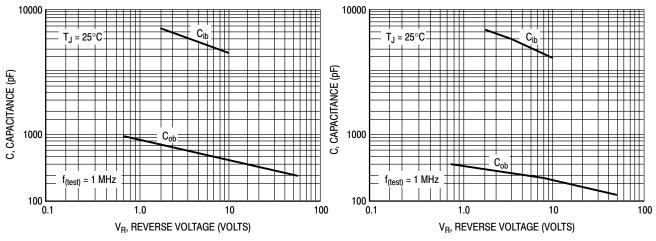


Figure 14. MJ21193 Typical Capacitance

Figure 15. MJ21194 Typical Capacitance

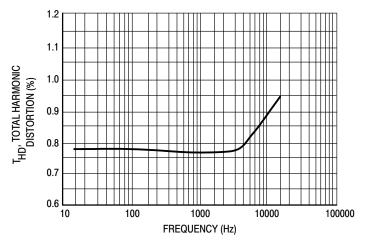
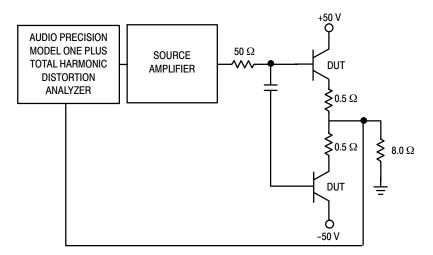
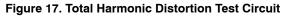


Figure 16. Typical Total Harmonic Distortion





MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



DIMENSIONS			
SCALE 1:1	TO–204 (TO–3) CASE 1–07 ISSUE Z)	DATE 05/18/1988
$ \begin{array}{c} $	$ \begin{array}{c} $	NOTES: 1. DIMENSIONING AND TC Y14.5M, 1982. 2. CONTROLLING DIMENS 3. ALL RULES AND NOTES REFERENCED TO-204A MIN MAX A 1.550 REF B 1.050 C 0.250 0.335 D 0.038 0.043 E 0.055 0.070 G 0.430 BSC H 0.215 BSC K 0.440 0.480 L 0.665 BSC N 0.830 Q 0.151 0.165 U 1.187 BSC V 0.131 0.188	ION: INCH.
STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR STYLE 6: PIN 1. GATE 2. EMITTER CASE: COLLECTOR	STYLE 2: STYLE 3: PIN 1. BASE PIN 1. GATE 2. COLLECTOR 2. SOURCE CASE: EMITTER CASE: DRAIN STYLE 7: STYLE 8: PIN 1. ANODE PIN 1. CATHODE #1 2. OPEN 2. CATHODE #2 CASE: CATHODE CASE: ANODE	STYLE 4: STYLE 5: PIN 1. GROUND 2. INPUT CASE: OUTPUT STYLE 9: PIN 1. ANODE #1 2. ANODE #2 CASE: CATHODE	E AL TRIP/DELAY

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